Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Isolated package
- · Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	95	А
T_j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 56 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	12	А
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 ^{\circ}\text{C; } Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	10	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _i = 25 °C; <u>Fig. 7</u>	-	22	70	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		
3	G	gate		T2—T1
mb	n.c.	mounting base; isolated		G sym051

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BT138X-800	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

7. Marking

Table 4. Marking codes

Type number	Marking code
BT138X-800	BT138X-800

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$\mathbf{I}_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \le 56$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	95	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	105	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	45	A ² s
dl _⊤ /dt	rate of rise of on-state	I _G = 70 mA; T2+ G+	-	50	A/µs
	current	I _G = 70 mA; T2+ G-	-	50	A/µs
		I _G = 70 mA; T2- G-	-	50	A/µs
		I _G = 140 mA; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

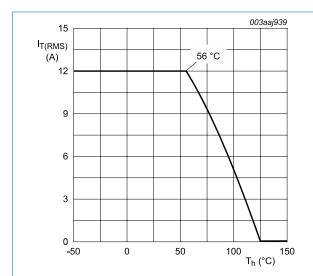
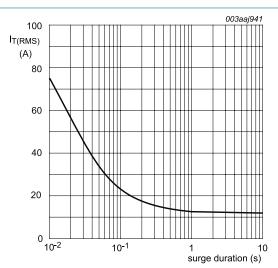


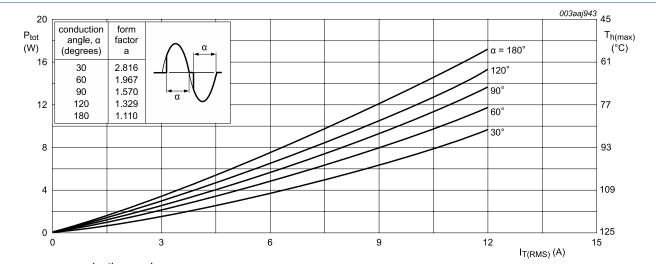
Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 56 ^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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 α = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

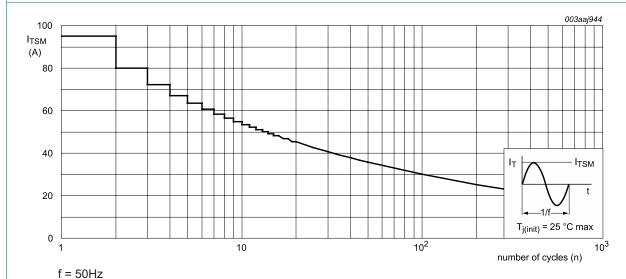
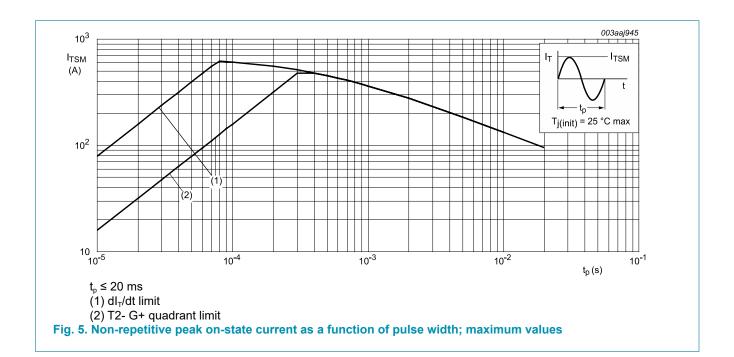


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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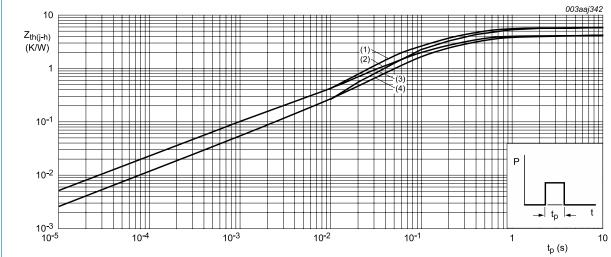


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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
1	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig. 6	-	-	4	K/W
	heatsink	full or half cycle; without heatsink compound; Fig. 6	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

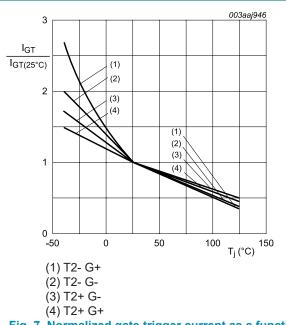
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cl	haracteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	10	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; $ $T_j = 25 \text{ °C}; Fig. 7$	-	22	70	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	40	μA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2 + G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	20	60	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$	-	8	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	10	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	6	30	mA
V _T	on-state voltage	I _τ = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 °C;$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynami	c characteristics		, 			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs
\mathbf{t}_{gt}	gate-controlled turn-on time	I_{TM} = 16 A; V_D = 800 V; I_G = 0.1 A; $d_{IG}/$ dt = 5 A/ μ s	-	2	-	μs



003aaj947 3 I_{L(25°C)} 2 -50 $_{T_{j}}^{100}$ $_{T_{j}}^{150}$

Fig. 8. Normalized latching current as a function of junction temperature



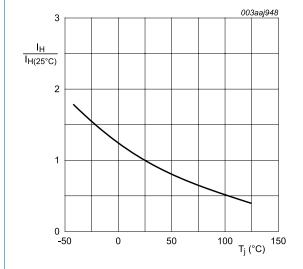
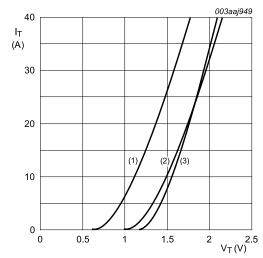


Fig. 9. Normalized holding current as a function of junction temperature

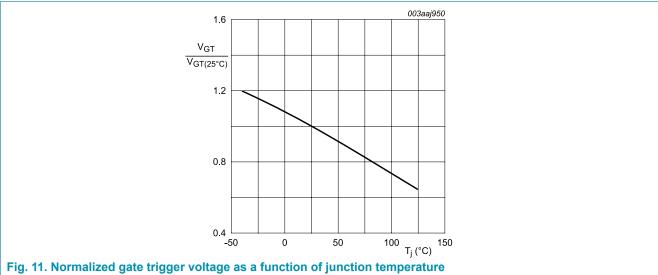


 V_o = 1.145 V; R_s = 0.031 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

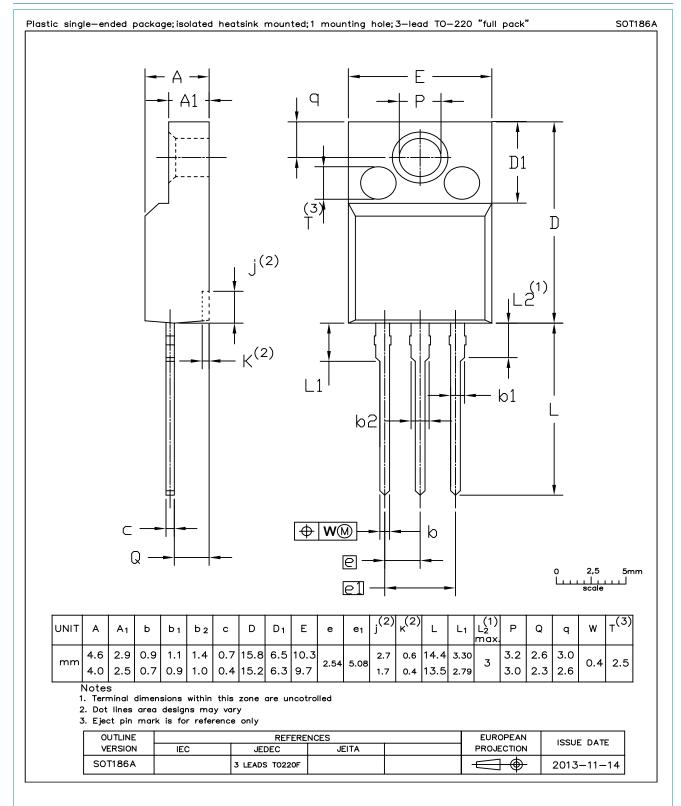
Fig. 10. On-state current as a function of on-state voltage

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12. Package outline



4Q Triad

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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